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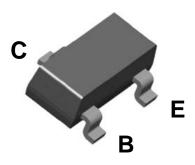
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June 2007

BSR17A

NPN General Purpose Amplifier



SOT-23 MARK: U92

Features

This device is designed as a general purpose amplifier and switch.

The useful dynamic range extends to 100 mA as a switch and to 100 MHz as an amplifier. Sourced from Process 23.

Absolute Maximum Ratings *Ta = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current (DC)	200	mA
TJ	Junction Temperature	-55 ~ +150	°C
T _{STG}	Storage Temperature	-55 ~ + 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

Thermal Characteristics *Ta = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
Po	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
R Θ JA	Thermal Resistance, Junction to Ambient	357	°C/W

^{*}Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics *T_a = 25°C unless otherwise noted

Parameter	Test Condition	MIN	MAX	Units
cteristics		·	•	
Collector-Emitter Breakdown Voltage	Ic = 1.0 mA, IB = 0	40		V
Collector-Base Breakdown Voltage	Ic = 10 μA, Iв = 0	60		V
Emitter-Base Breakdown Voltage	Ic = 10 μA, Iв = 0	6.0		V
Collector-Cutoff Current	Vcb = 30 V, TA = 150°C		5.0	μΑ
Emitter-Cutoff Current	VCE = 30 V, VEB = 3.0 V		50	nA
IBEX Reverse Base Current	VCE = 30 V, VEB = 3.0 V		50	nA
	Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Cutoff Current Emitter-Cutoff Current	Collector-Emitter Breakdown Voltage Ic = 1.0 mA, IB = 0	Ceteristics Collector-Emitter Breakdown Voltage Ic = 1.0 mA, Iв = 0 40 Collector-Base Breakdown Voltage Ic = 10 μA, Iв = 0 60 Emitter-Base Breakdown Voltage Ic = 10 μA, Iв = 0 6.0 Collector-Cutoff Current VcB = 30 V, TA = 150°C Emitter-Cutoff Current VcE = 30 V, VeB = 3.0 V	Ceteristics Collector-Emitter Breakdown Voltage Ic = 1.0 mA, I _B = 0 40 Collector-Base Breakdown Voltage Ic = 10 μA, I _B = 0 60 Emitter-Base Breakdown Voltage Ic = 10 μA, I _B = 0 6.0 Collector-Cutoff Current V _{CB} = 30 V, T _A = 150°C 5.0 Emitter-Cutoff Current V _{CE} = 30 V, V _{EB} = 3.0 V 50

On Characteristics

hfE	DC Current Gain	Ic = 0.1 mA, VcE = 1.0 V Ic = 1.0 mA, VcE = 1.0 V Ic = 10 mA, VcE = 1.0 V Ic = 50 mA, VcE = 1.0 V Ic = 100 mA, VcE = 1.0 V	40 70 100 60 30	300	
VCE(sat)	Collector-Emitter Saturation Voltage *	Ic = 10 mA, I _B = 1.0 mA Ic = 50 mA, I _B = 5.0 mA		0.2 0.3	V V
V _{BE} (sat)	Emitter-Base Breakdown Voltage *	Ic = 10 mA, I _B = 1.0 mA Ic = 50 mA, I _B = 5.0 mA	0.65	0.85 0.95	V V

Small Signal Characteristics

f⊤	Transition Frequency	Ic = 20 mA, VcE = 20 V, f = 100 MHz	300		MHz
Ccb	Collector-Base Capacitance	VcB = 0.5 V, IE = 0, f = 1.0 MHz		4.0	pF
Ceb	Emitter-Base Capacitance	V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz		8.0	pF
hie	Input Impedance	VcE= 10 V,lc= 1.0 mA,f=1.0 kHz	1.0	10	kΩ
hfe	Small-Signal Current Gain	VcE= 10 V,lc= 1.0 mA,f=1.0 kHz	100	400	
hoe	Output Admittance	VcE= 10 V,Ic= 1.0 mA,f=1.0 kHz	1.0	40	μS

Switching Characteristics

td	Delay Time	Ic = 10 mA, Iв1 = 1.0 mA,VEB= 0.5 V	35	ns
tr	Rise Time		4.0	pF
ts	Storage Time	Ic = 10 mA, IBon = IBoff = 1.0 mA	200	ns
tf	Fall Time		50	ns

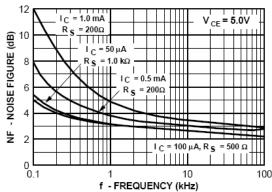
^{*}Pulse Test: Pulse Width 300 s, Duty Cycle 2.0 %

Spice Model

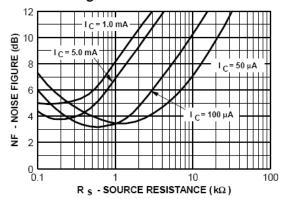
NPN (Is=6.734f Xti=3 Eg=1.11 Vaf=74.03 Bf=416.4 Ne=1.259 Ise=6.734 Ikf=66.78m Xtb=1.5 Br=.7371 Nc=2 Isc=0 Ikr=0 Rc=1 Cjc=3.638p Mjc=.3085 Vjc=.75 Fc=.5 Cje=4.493p Mje=.2593 Vje=.75 Tr=239.5n Tf=301.2p Itf=.4 Vtf=4 Xtf=2 Rb=10)

Typical Performance Characteristics

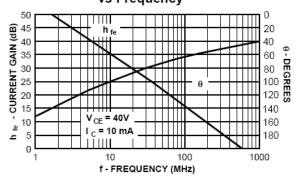
Noise Figure vs Frequency



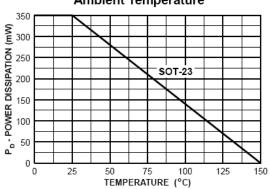
Noise Figure vs Source Resistance



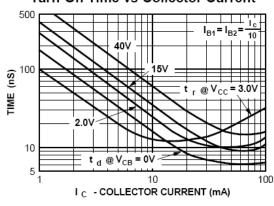
Current Gain and Phase Angle vs Frequency



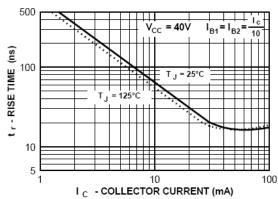
Power Dissipation vs Ambient Temperature



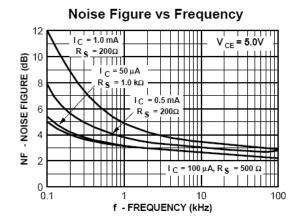
Turn-On Time vs Collector Current

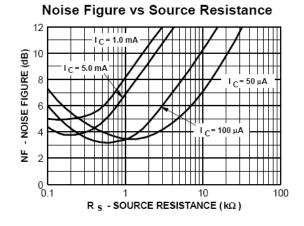


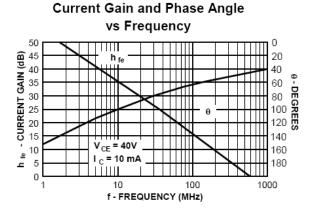
Rise Time vs Collector Current

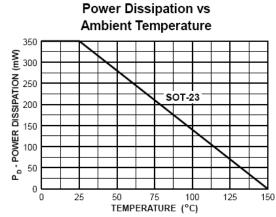


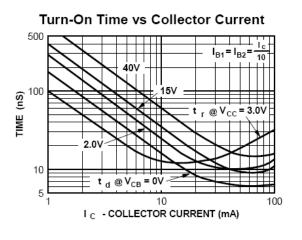
Typical Performance Characteristics (continued)

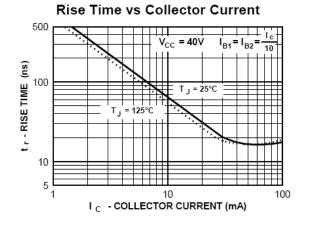






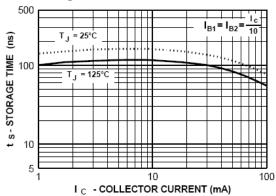




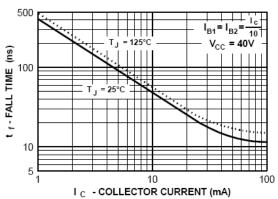


Typical Performance Characteristics (continued)

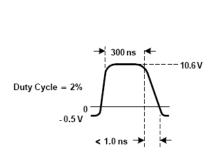
Storage Time vs Collector Current



Fall Time vs Collector Current



Test Circuits



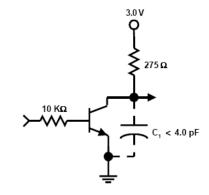
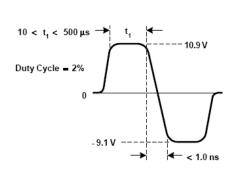


FIGURE 1: Delay and Rise Time Equivalent Test Circuit



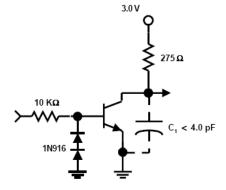


FIGURE 2: Storage and Fall Time Equivalent Test Circuit





UniFET™

 VCX^{TM}

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